Silicon NPN Epitaxial

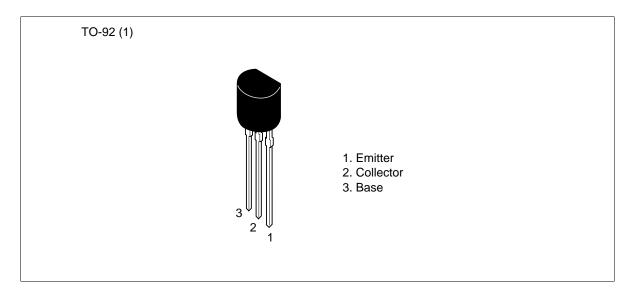
HITACHI

ADE-208-1052A (Z) 2nd. Edition Mar. 2001

Application

Low frequency low noise amplifier

Outline





Absolute Maximum Ratings (Ta = 25°C)

Item	Symbol	2SC1344	2SC1345	Unit
Collector to base voltage	V_{CBO}	30	55	V
Collector to emitter voltage	V _{CEO}	30	50	V
Emitter to base voltage	V_{EBO}	5	5	V
Collector current	I _c	100	100	mA
Collector power dissipation	P _c	200	200	mW
Junction temperature	Tj	150	150	°C
Storage temperature	Tstg	-55 to +150	-55 to +150	°C

Electrical Characteristics ($Ta = 25^{\circ}C$)

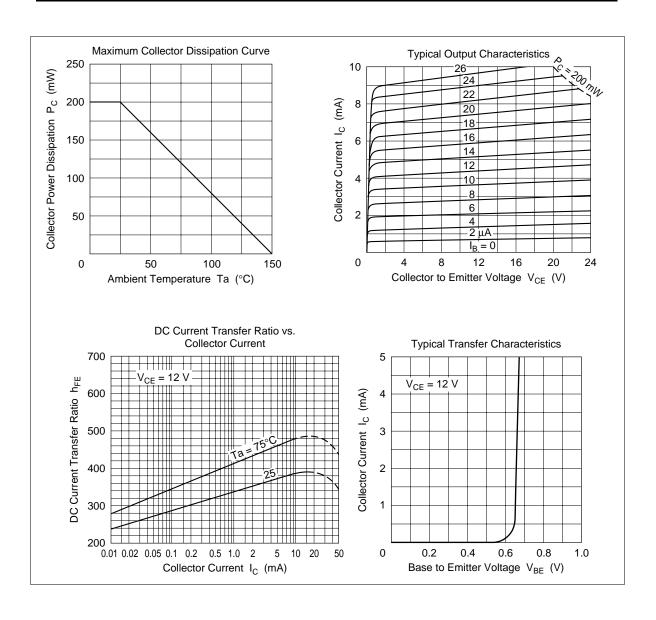
		2SC1	344		2SC1345				
Item	Symbol	Min	Тур	Max	Min	Тур	Max	Unit	Test conditions
Collector to base breakdown voltage	$V_{(BR)CBO}$	30	_	_	55	_	_	V	$I_{\rm C} = -10 \; \mu A, \; I_{\rm E} = 0$
Collector to emitter breakdown voltage	$V_{(BR)CEO}$	30	_	_	50	_	_	V	$I_{\rm C}$ = 1 mA, $R_{\rm BE}$ = ∞
Emitter to base breakdown voltage	$V_{(BR)EBO}$	5	_	_	5	_	_	V	$I_E = 10 \mu A, I_C = 0$
Collector cutoff current	I _{CBO}	_	_	0.5	_	_	0.5	μΑ	$V_{CB} = 18 \text{ V}, I_{E} = 0$
Emitter cutoff current	I _{EBO}	_	_	0.5	_	_	0.5	μΑ	$V_{EB} = 2 \text{ V}, I_{C} = 0$
DC current transfer ratio	h _{FE} *1	250	_	1200	250	_	1200		$V_{CE} = 12 \text{ V}, I_{C} = 2 \text{ mA}$
Base to emitter voltage	V_{BE}	_	_	0.75	_	_	0.75	V	$V_{CE} = 12 \text{ V}, I_{C} = 2 \text{ mA}$
Collector to emitter saturation voltage	$V_{\text{CE(sat)}}$	_	_	0.5	_	_	0.5	V	$I_{\rm C}$ = 10 mA, $I_{\rm B}$ = 1 mA
Gain bandwidth product	f _T	_	230	_	_	230	_	MHz	$V_{CE} = 12 \text{ V}, I_{C} = 2 \text{ mA}$
Collector output capacitance	Cob	_	_	3.5	_	_	3.5	pF	$V_{CB} = 10 \text{ V}, I_{E} = 0,$ f = 1 MHz
Noise figure	NF	_		8			8	dB	$V_{CE} = 6 \text{ V}, I_{C} = 0.1 \text{ mA},$ $f = 10 \text{ Hz}, R_{g} = 10 \text{ k}\Omega$
		_	_	1	_	_	1	dB	$V_{CE} = 6 \text{ V}, I_{C} = 0.1 \text{ mA},$ $f = 1 \text{ kHz}, R_{g} = 10 \text{ k}\Omega$

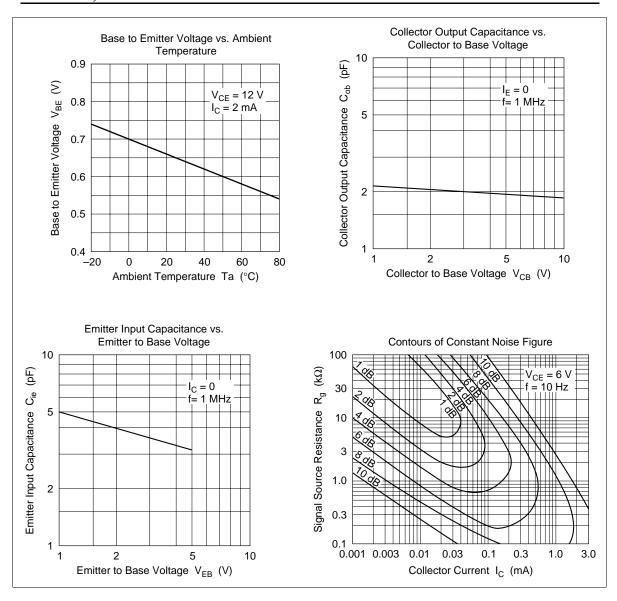
Note: 1. The 2SC1344 and 2SC1345 are grouped by h_{FE} as follows.

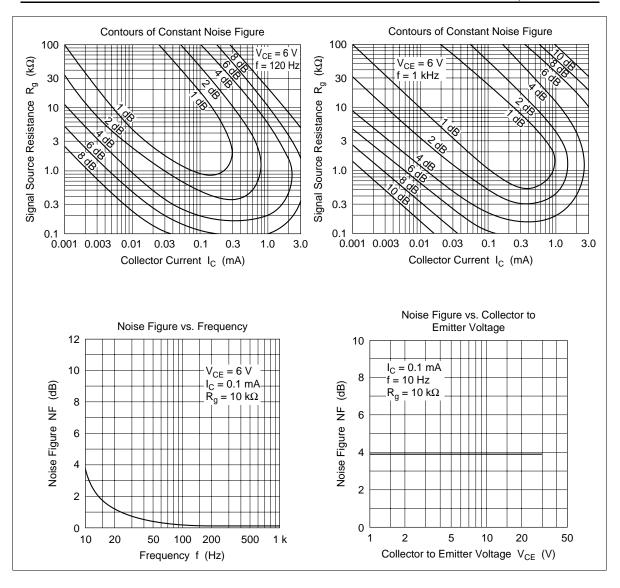
D	E	F
250 to 500	400 to 800	600 to 1200

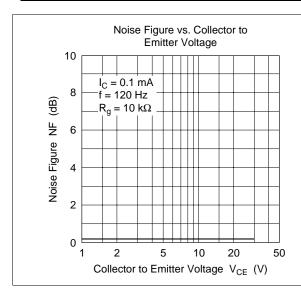
Small Signal h Parameters ($V_{CE} = 5V$, $I_{C} = 0.1$ mA, f = 270 Hz, Ta = 25°C, Emitter common)

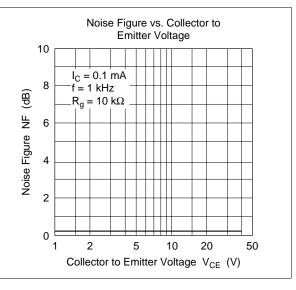
Item	Symbol	D	E	F	Unit
Input impedance	hie	110	170	240	kΩ
Voltage feedback ratio	hre	9.5	14.5	16	× 10 ⁻⁴
Current transfer ratio	hfe	340	540	825	
Output admittance	hoe	12.0	12.5	13.5	μS



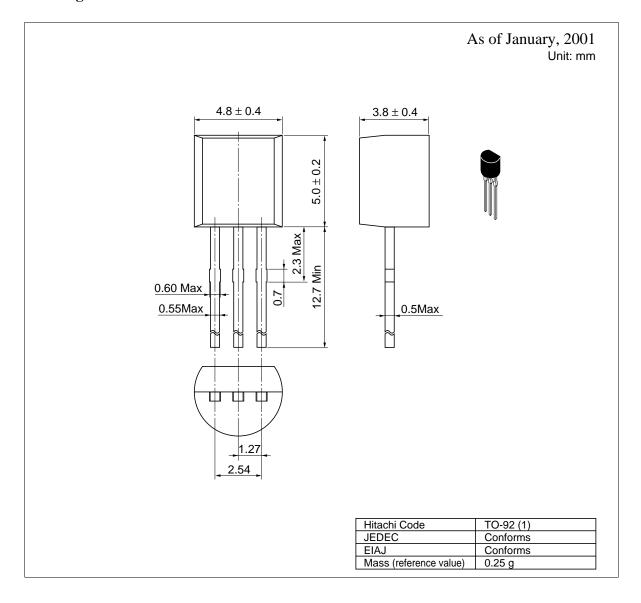








Package Dimensions



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